

# Gagik A Oganesyanyan

## List of Publications by Year in descending order

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78  
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#	ARTICLE	IF	CITATIONS
1	Electron- and proton irradiation of strongly doped silicon of p-type: Formation and annealing of boron-related defects. <i>Journal of Applied Physics</i> , 2022, 131, 125705.	2.5	3
2	Microstructure of bismuth centers in silicon before and after irradiation with 15 MeV protons. <i>Journal of Physics Condensed Matter</i> , 2021, 33, 245702.	1.8	0
3	Towards the Modeling of Impurity-Related Defects in Irradiated n-Type Germanium: a Challenge to Theory. <i>Semiconductors</i> , 2020, 54, 1388-1394.	0.5	0
4	Vacancy-Phosphorus Complexes in Electron-Irradiated Floating-Zone n-Type Silicon: New Points in Annealing Studies. <i>Semiconductors</i> , 2020, 54, 46-54.	0.5	0
5	Interaction Rates of Group-III and Group-V Impurities with Intrinsic Point Defects in Irradiated Si and Ge. <i>Semiconductors</i> , 2018, 52, 1677-1685.	0.5	0
6	Radiation-produced defects in germanium: Experimental data and models of defects. <i>Semiconductors</i> , 2017, 51, 1571-1587.	0.5	3
7	Effect of irradiation with 15-MeV protons on the compensation of Ge@Sb conductivity. <i>Journal of Surface Investigation</i> , 2017, 11, 601-605.	0.5	0
8	Effects of irradiation with 8-MeV protons on n-3C-SiC heteroepitaxial layers. <i>Semiconductors</i> , 2017, 51, 1044-1046.	0.5	0
9	Positron probing of open vacancy volume of phosphorus-vacancy complexes in float-zone n-type silicon irradiated by 0.9-MeV electrons and by 15-MeV protons. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2017, 14, 1700120.	0.8	1
10	Specific features of proton interaction with transistor structures having a 2D AlGaIn/GaN channel. <i>Technical Physics Letters</i> , 2016, 42, 1079-1082.	0.7	2
11	Positron annihilation lifetime in float-zone n-type silicon irradiated by fast electrons: a thermally stable vacancy defect. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016, 13, 807-811.	0.8	3
12	Effect of the energy of recoil atoms on conductivity compensation in moderately doped n-Si and n-SiC under irradiation with MeV electrons and protons. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 2016, 384, 100-105.	1.4	7
13	The relationship between the reliability of transistors with 2D AlGaIn/GaN channel and organization type of nanomaterial. <i>Technical Physics Letters</i> , 2016, 42, 701-703.	0.7	6
14	Some challenging points in the identification of defects in floating-zone n-type silicon irradiated with 8 and 15 MeV protons. <i>Semiconductors</i> , 2016, 50, 1291-1298.	0.5	8
15	Positron probing of phosphorus-vacancy complexes in silicon irradiated with 15 MeV protons. <i>Journal of Physics: Conference Series</i> , 2015, 618, 012013.	0.4	1
16	Monovacancy-As complexes in proton-irradiated Ge studied by positron lifetime spectroscopy. <i>Acta Materialia</i> , 2015, 83, 473-478.	7.9	10
17	Formation and annealing of vacancy-P complexes in proton-irradiated germanium. <i>Acta Materialia</i> , 2015, 100, 1-10.	7.9	11
18	Donor-vacancy pairs in irradiated n-Ge: A searching look at the problem. , 2014, , .		1

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19	Cascade phonon-assisted trapping of positrons by divacancies in n-FZ-Si(P) single crystals irradiated with 15 MeV protons. AIP Conference Proceedings, 2014, , .	0.4	3
20	Electrical properties of diluted n- and p-Si1 $\hat{\alpha}$ x Ge x at small x. Semiconductors, 2014, 48, 1552-1556.	0.5	3
21	Vacancy-donor pairs and their formation in irradiated n-Si. Semiconductors, 2014, 48, 1438-1443.	0.5	12
22	Positron annihilation on defects in silicon irradiated with 15 MeV protons. Journal of Physics Condensed Matter, 2013, 25, 035801.	1.8	17
23	P-6H-SiC Conductivity Compensation after Irradiation of 8MeV Protons. Materials Science Forum, 2013, 740-742, 353-356.	0.3	0
24	Similarities and distinctions of defect production by fast electron and proton irradiation: Moderately doped silicon and silicon carbide of n-type. Semiconductors, 2012, 46, 456-465.	0.5	31
25	Reverse recovery of Si/Si1 $\hat{\alpha}$ x Ge x heterodiodes fabricated by direct bonding. Technical Physics Letters, 2011, 37, 632-635.	0.7	1
26	Conductivity compensation in p-6H-SiC in irradiation with 8-MeV protons. Semiconductors, 2011, 45, 1145-1147.	0.5	2
27	Comparative study of changes in electrical properties of silicon and silicon carbide upon proton irradiation. Semiconductors, 2010, 44, 678-684.	0.5	9
28	Electrical characteristics of multigraphene films grown on high-resistivity silicon carbide substrates. Semiconductors, 2010, 44, 1389-1391.	0.5	4
29	10.1007/s11453-008-2023-8. , 2010, 42, 242.		0
30	Metal-insulator transition in n-3C-SiC epitaxial films. Journal of Applied Physics, 2009, 105, 023706.	2.5	6
31	The Production of Vacancy-Oxygen Defects in Electron-Irradiated Cz-Si Initially Treated at High Temperatures and High Pressures. Solid State Phenomena, 2009, 156-158, 123-128.	0.3	3
32	Electrically active defects in erbium-implanted silicon: Effects of annealing under high hydrostatic pressures and electron irradiation. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 159-160, 157-159.	3.5	0
33	Influence of the defect density (twins boundaries) on electrical parameters of 3C-SiC epitaxial films. Physica B: Condensed Matter, 2009, 404, 4758-4760.	2.7	13
34	Charge carrier removal rates in n-type silicon and silicon carbide subjected to electron and proton irradiation. Physica B: Condensed Matter, 2009, 404, 4752-4754.	2.7	16
35	Effects of germanium doping on the behavior of oxygen and carbon impurities and impurity-related complexes in Si. Physica B: Condensed Matter, 2009, 404, 4693-4697.	2.7	12
36	Electrical properties of thermal donors formed in silicon under elastic tensile stress. Journal of Surface Investigation, 2009, 3, 962-965.	0.5	2

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37	Metal-insulator transition in n-3C-SiC epitaxial films. <i>Semiconductors</i> , 2009, 43, 318-322.	0.5	0
38	Quantum supercurrent and Andreev reflection in silicon nanostructures. <i>Semiconductors</i> , 2009, 43, 1455-1465.	0.5	4
39	Spin-dependent transport of holes in silicon quantum wells confined by superconductor barriers. <i>Physica C: Superconductivity and Its Applications</i> , 2008, 468, 840-843.	1.2	15
40	Negative magnetoresistance in SiC heteropolytype junctions. <i>Journal of Materials Science: Materials in Electronics</i> , 2008, 19, 793-796.	2.2	2
41	The effect of germanium doping on the evolution of defects in silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2008, 154-155, 133-136.	3.5	16
42	Effect of electron irradiation on carrier removal rate in silicon and silicon carbide with 4H modification. <i>Semiconductors</i> , 2008, 42, 242-247.	0.5	16
43	Highly doped p-type 3C-SiC on 6H-SiC substrates. <i>Semiconductor Science and Technology</i> , 2008, 23, 075004.	2.0	17
44	Radiation-produced defects in n-GaN. <i>Physica B: Condensed Matter</i> , 2007, 401-402, 315-318.	2.7	6
45	IR studies of oxygen-vacancy defects in electron-irradiated Ge-doped Si. <i>Physica B: Condensed Matter</i> , 2007, 401-402, 487-490.	2.7	12
46	Features of the formation of thermal donors in silicon under elastic tensile stress. <i>Journal of Surface Investigation</i> , 2007, 1, 294-297.	0.5	2
47	Galvanomagnetic properties of 3C-SiC epilayers grown on hexagonal SiC substrates. <i>Technical Physics Letters</i> , 2007, 33, 1035-1037.	0.7	2
48	Formation rate of vacancy-oxygen complexes in heat-treated Czochralski grown silicon under gamma-irradiation. <i>Journal of Materials Science: Materials in Electronics</i> , 2007, 18, 701-704.	2.2	2
49	"New Donors" in Czochralski Grown Silicon Annealed at $\approx 600^\circ\text{C}$ under Compressive Stress. <i>Solid State Phenomena</i> , 2005, 108-109, 181-186.	0.3	1
50	Oxygen agglomeration and formation of oxygen-related thermal donors in heat-treated silicon. <i>Crystal Research and Technology</i> , 2003, 38, 394-398.	1.3	6
51	Stress-induced changes of thermal donor formation in heat-treated Czochralski-grown silicon. <i>Physica B: Condensed Matter</i> , 2003, 340-342, 769-772.	2.7	8
52	Photoluminescence characterization of thermal defects in Czochralski grown silicon heat treated at $600^\circ\text{C}$ . <i>Physica B: Condensed Matter</i> , 2003, 340-342, 1018-1021.	2.7	1
53	Double thermal donors in Czochralski-grown silicon heat-treated under atmospheric and high hydrostatic pressures. <i>Physica Status Solidi (B): Basic Research</i> , 2003, 235, 75-78.	1.5	25
54	Shallow donor centers in gallium nitrides. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 601-604.	0.8	5

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55	Impact of Compressive Stress on the Formation of Thermal Donors in Heat-Treated Silicon. Solid State Phenomena, 2002, 82-84, 259-266.	0.3	0
56	Investigation of vacancy-type complexes in GaN and AlN using positron annihilation. Semiconductors, 2002, 36, 1106-1110.	0.5	3
57	<title>Peculiarities of the thermal donor formation in Czochralski-grown silicon under high hydrostatic pressure</title>. , 2001, , .		3
58	Radiation-induced defects in n-type GaN and InN. Physica B: Condensed Matter, 2001, 308-310, 58-61.	2.7	25
59	Low-temperature photoluminescence characterization of defects formation in hydrogen and helium implanted silicon at post-implantation annealing. Physica B: Condensed Matter, 2001, 308-310, 181-184.	2.7	15
60	Shallow donors in silicon coimplanted with rare-earth ions and oxygen. Physica B: Condensed Matter, 2001, 308-310, 350-353.	2.7	5
61	Title is missing!. Journal of Materials Science: Materials in Electronics, 2001, 12, 223-225.	2.2	7
62	Thermal Donors in Silicon Implanted with Rare Earth Impurities. Solid State Phenomena, 2001, 82-84, 93-98.	0.3	2
63	Formation of deep thermal donors in heat-treated Czochralski silicon. Applied Physics Letters, 1996, 68, 2375-2377.	3.3	12
64	New Donors in Heat-Treated Cz-Si, Their Components and Formation Kinetics. Solid State Phenomena, 1995, 47-48, 259-266.	0.3	7
65	EPR/ENDOR Investigation on the Nature of Heat Treatment Centers in Silicon. Materials Science Forum, 1994, 143-147, 141-146.	0.3	12
66	On the nature and structures of different heat treatment centres in n- and p-type silicon. Semiconductor Science and Technology, 1994, 9, 1346-1353.	2.0	4
67	Peculiarities in the Defect Behavior in Heat-Treated Cz-Si with a Low and High Oxygen Content. Solid State Phenomena, 1993, 32-33, 173-180.	0.3	1
68	Galvanomagnetic Properties of 3C-SiC/6H-SiC Heterostructures. Materials Science Forum, 0, 600-603, 541-544.	0.3	0
69	Investigation of the Metal-Insulator Transition in n-3C-SiC Epitaxial Films. Materials Science Forum, 0, 615-617, 335-338.	0.3	0
70	P-Type 3C-SiC Grown by Sublimation Epitaxy on 6H-SiC Substrates. Materials Science Forum, 0, 615-617, 177-180.	0.3	0
71	Low Temperature near Band Gap Photoluminescence of 3C-SiC/15R-SiC and 3C-SiC/6H-SiC Heterostructures. Materials Science Forum, 0, 645-648, 259-262.	0.3	0
72	Positron Probing of Point Radiation Defects in Proton - Irradiated FZ-Silicon Single Crystals. Solid State Phenomena, 0, 178-179, 313-318.	0.3	1

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73	Electron Mobility in Moderately Doped Si <sub>1-x</sub> Ge <sub>x</sub> . Solid State Phenomena, 0, 178-179, 31-34.	0.3	0
74	Positron Lifetime at Deep Donors of Radiation Origin in Proton - Irradiated FZ-Silicon Single Crystals. Materials Science Forum, 0, 733, 224-227.	0.3	2
75	Positron Probing of Vacancy Volume of Thermally Stable Deep Donors Produced with 15 MeV Protons in n-FZ-Si:P Crystals. Solid State Phenomena, 0, 205-206, 317-322.	0.3	4
76	Production and Annealing of Defects in Proton-Irradiated n-Ge. Solid State Phenomena, 0, 205-206, 422-426.	0.3	1
77	Similarity of Atomic Configurations of Thermally Stable Positron-Sensitive Complexes Produced with 0.9-MeV Electrons and 15-MeV Protons in n-FZ-Si:P Crystals. Solid State Phenomena, 0, 242, 296-301.	0.3	2
78	Electrical Properties of Defects in Ga-Doped Ge Irradiated with Fast Electrons and Protons. Solid State Phenomena, 0, 242, 316-321.	0.3	0